

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing a double-sided flexible printed board, comprising the following steps of:

- (A) forming a polyimide precursor layer on a metal layer;
- (B) forming an upper circuit layer on the polyimide precursor layer by a semi-additive technique, leaving the polyimide precursor layer partially exposed;exposed at the upper circuit layer side; and
- (C) imidating the partially exposed polyimide precursor layer to form a polyimide insulating layer.

2. (Original) The method according to claim 1, wherein step (M) in which the formation of a through hole for ensuring conductivity between the metal layer and the upper circuit layer is performed between step (B) and step (C) or subsequent to step (C).

3. (Currently Amended) A method for manufacturing a double-sided flexible printed board, comprising the following steps of:

- (A) forming a polyimide precursor layer on a metal layer;
- (B) forming an upper circuit layer on the polyimide precursor layer by a semi-additive technique;technique, leaving the polyimide precursor layer partially exposed at the upper circuit layer side; and
- (C) imidating the polyimide precursor layer, while the polyimide precursor layer includes the upper circuit layer that has been formed on the polyimide precursor layer, to form a polyimide insulating layer.

4. (Previously Presented) The method according to claim 3, wherein step (M) in which the formation of a through hole for ensuring conductivity between the metal layer and the upper circuit layer is performed between step (B) and step (C) or subsequent to step (C).

5. (Currently Amended) A method for manufacturing a double-sided flexible printed board, comprising the following steps of:

- (A) forming a polyimide precursor layer on a metal layer;
- (B) forming an upper circuit layer on the polyimide precursor layer by a semi-additive ~~technique; technique, leaving the polyimide precursor layer partially exposed at the upper circuit layer side; and~~
- (C) after step (B), imidating the polyimide precursor layer to form a polyimide insulating layer.

6. (Previously Presented) The method according to claim 5, wherein step (M) in which the formation of a through hole for ensuring conductivity between the metal layer and the upper circuit layer is performed between step (B) and step (C) or subsequent to step (C).